

Data Sheet January 2000 File Number 3106.3

50A, 1000V Hyperfast Diode

The RHRG50100 is a hyperfast diode with soft recovery characteristics (t_{rr} < 75ns). It has half the recovery time of ultrafast diodes and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

Formerly developmental type TA49066.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RHRG50100	TO-247	RHRG50100

NOTE: When ordering, use the entire part number.

Symbol



Features

•	Hyperfast with Soft Recovery	75ns
•	Operating Temperature	75 ⁰ C
•	Reverse Voltage	V000

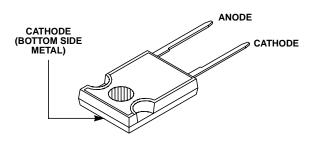
- · Avalanche Energy Rated
- Planar Construction

Applications

- · Switching Power Supplies
- · Power Switching Circuits
- · General Purpose

Packaging

JEDEC STYLE TO-247



Absolute Maximum Ratings $T_C = 25^{\circ}C$

	RHRG50100	UNITS
Peak Repetitive Reverse VoltageV _{RRM}	1000	V
Working Peak Reverse Voltage	1000	V
DC Blocking Voltage	1000	V
Average Rectified Forward Current	50	Α
Repetitive Peak Surge Current	100	Α
Nonrepetitive Peak Surge Current	500	Α
Maximum Power Dissipation	150	W
Avalanche Energy (See Figures 7 and 8)	40	mJ
Operating and Storage Temperature	-65 to 175	οС

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V _F	I _F = 50A	-	-	3.0	V
	$I_F = 50A, T_C = 150^{\circ}C$	-	-	2.5	V
I _R	V _R = 1000V	-	-	250	μА
	$V_R = 1000V, T_C = 150^{\circ}C$	-	-	3.0	mA
t _{rr}	$I_F = 1A$, $dI_F/dt = 100A/\mu s$	-	-	75	ns
	$I_F = 50A$, $dI_F/dt = 100A/\mu s$	-	-	95	ns
t _a	$I_F = 50A$, $dI_F/dt = 100A/\mu s$	-	54	-	ns
t _b	$I_F = 50A$, $dI_F/dt = 100A/\mu s$	-	32	-	ns
$R_{ heta JC}$		-	-	1.0	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

 I_R = Instantaneous reverse current.

 t_{rr} = Reverse recovery time (See Figure 6), summation of $t_a + t_b$.

t_a = Time to reach peak reverse current (See Figure 6).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

Typical Performance Curves

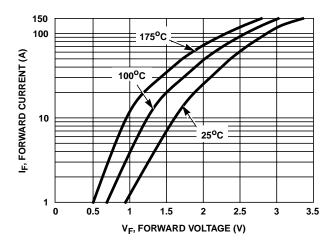


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

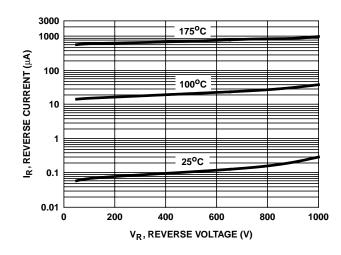


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

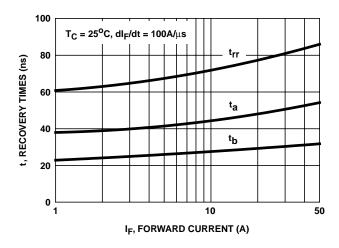


FIGURE 3. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

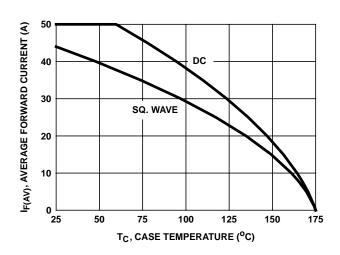


FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

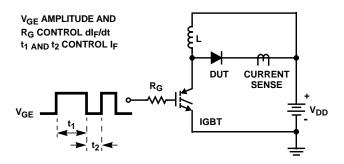


FIGURE 5. t_{rr} TEST CIRCUIT

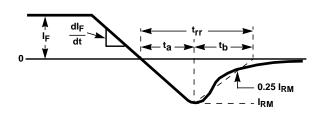


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

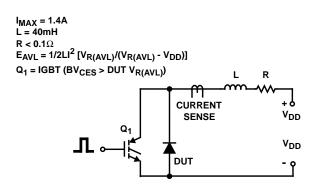


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

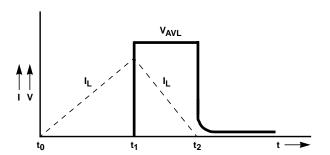


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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